

4. (Amended) An interconnection comprising:

C1
an aluminum copper titanium alloy layer, wherein the aluminum-copper-titanium alloy layer comprises less than 0.57 atomic percent titanium, about 0.5 atomic percent copper and the remainder is aluminum.

5. (Amended) The interconnection of claim 4, wherein the aluminum-copper-titanium alloy layer comprises about 0.1 atomic percent titanium.

C2
9. (Amended) An interconnection formed on a substrate of an integrated circuit comprising an aluminum-copper-titanium alloy layer, wherein the aluminum-copper-titanium alloy layer comprises less than 0.57 atomic percent titanium, about 0.5 atomic percent copper and the remainder is aluminum.

10. (Amended) The interconnection of claim 9, wherein the aluminum-copper-titanium alloy layer contains about 0.1 atomic percent titanium.

14. (Amended) An integrated circuit comprising:

a substrate; and

C3
an interconnection level disposed about the substrate, the interconnection level having an aluminum-copper-titanium alloy layer, wherein the aluminum-copper-titanium alloy layer comprises less than 0.57 atomic percent titanium, about 0.5 atomic percent copper and the remainder is aluminum.

15. (Amended) The integrated circuit of claim 14, wherein the aluminum-copper-titanium alloy layer contains about 0.1 atomic percent titanium.

16. (Amended) A multilayered interconnection structure formed on a substrate, the interconnection comprising:

a first titanium layer;

a first titanium nitride layer;